Product data sheet

### 1. General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

PNP complement: PBSS5330PAS

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain ( $h_{\text{FE}}$ ) at high  $I_{\text{C}}$
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

# 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	30	V
I <sub>C</sub>	collector current		-	-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le$ 300 μs; $δ \le$ 0.02; $T_{amb}$ = 25 °C	-	75	100	mΩ



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	E	emitter		1-
3	С	collector		2 sym021
			Transparent top view DFN2020D-3 (SOT1061D)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4330PAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4330PAS	E1

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## 8. Limiting values

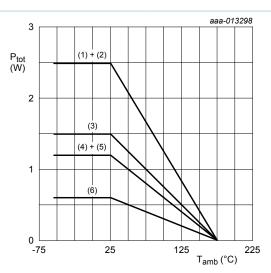
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	5	Α
I <sub>B</sub>	base current			-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	600	mW
			[2][3]	-	1.2	W
			[4]	-	1.5	W
			[5][6]	-	2.5	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [6] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

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- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (4) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			[1]	-	-	250	K/W
	-		[2][3]	-	-	125	K/W
	ambient		[4]	-	-	100	K/W
			[5][6]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [6] Device mounted on a FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

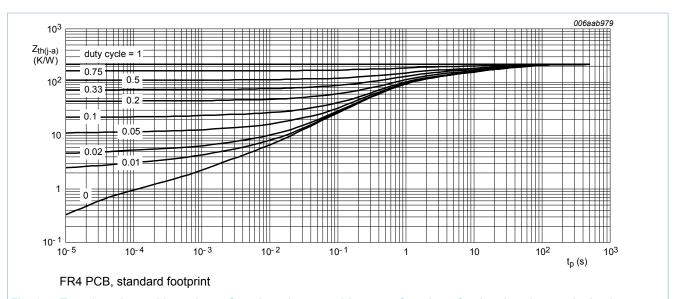


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

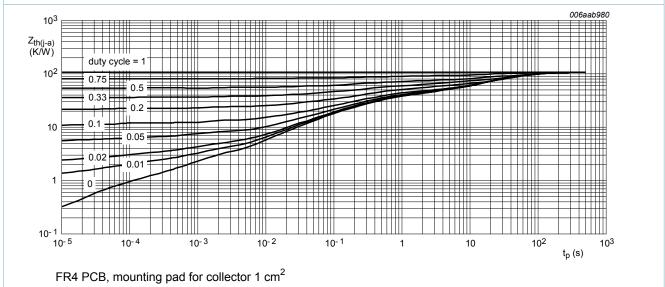


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

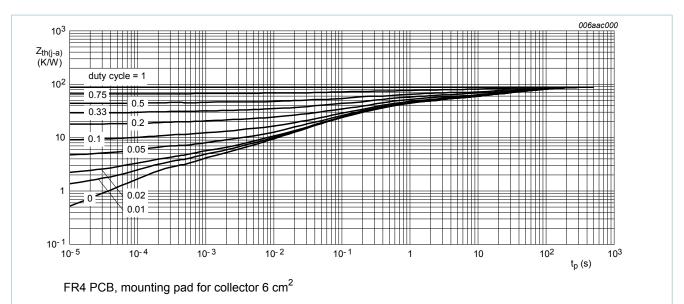


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

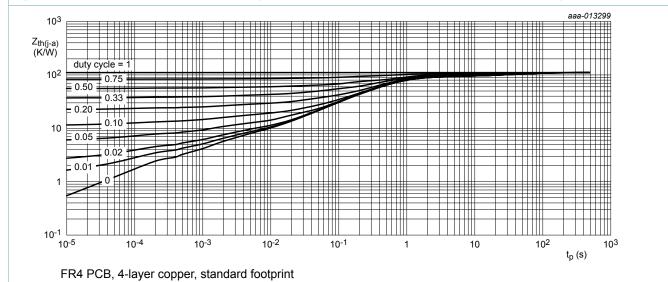
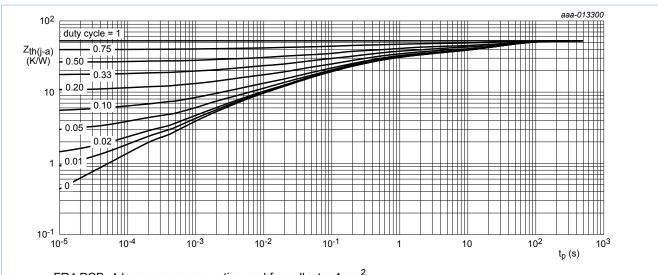


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, mounting pad for collector 1 cm<sup>2</sup>

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

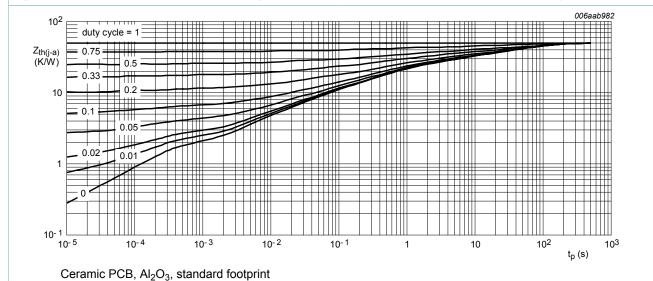


Fig. 7. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

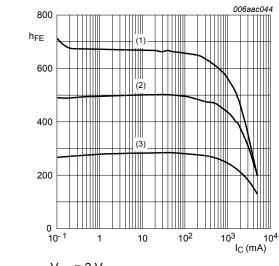
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	$V_{CB}$ = 24 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 24 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
l <sub>ЕВО</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	300	465	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	270	435	700	
		$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	230	370	-	
	$V_{CE}$ = 2 V; $I_{C}$ = 3 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	180	310	-		
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 0.5 A; $I_B$ = 50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	40	60	mV
		$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	80	110	mV
		$I_{C}$ = 2 A; $I_{B}$ = 100 mA; pulsed; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	155	220	mV
		$I_C$ = 3 A; $I_B$ = 300 mA; pulsed;	-	220	300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	75	100	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = 2 A; $I_{B}$ = 100 mA; pulsed; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.95	1.1	V
		$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	1.07	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.76	1	V
t <sub>d</sub>	delay time	$V_{CC} = 9 \text{ V}; I_C = 2 \text{ A}; I_{Bon} = 0.1 \text{ A};$	-	11	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	52	-	ns
t <sub>on</sub>	turn-on time		-	63	-	ns
t <sub>s</sub>	storage time		-	230	-	ns
t <sub>f</sub>	fall time		-,	40	-	ns
t <sub>off</sub>	turn-off time		-	270	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	210	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	21	30	pF



 $V_{CE} = 2 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. DC current gain as a function of collector current; typical values

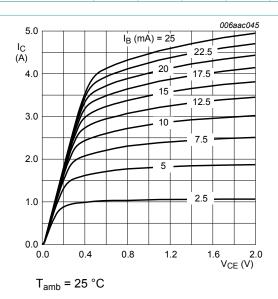
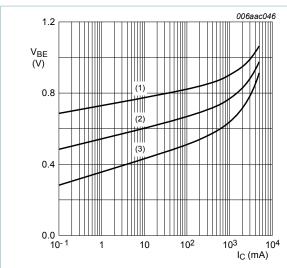


Fig. 9. Collector current as a function of collectoremitter voltage; typical values



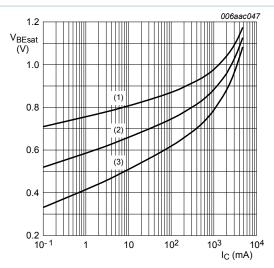
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 10. Base-emitter voltage as a function of collector current; typical values



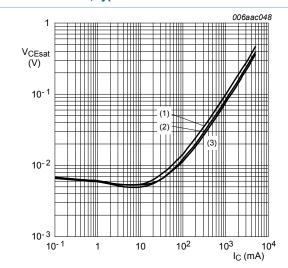
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



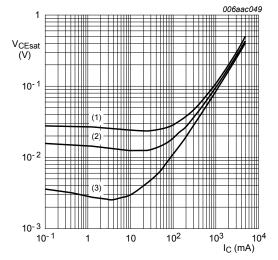
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

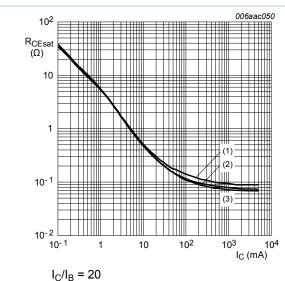


(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



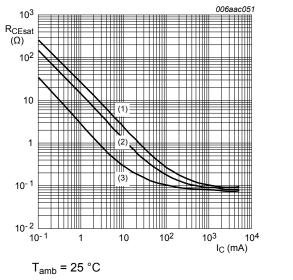
$$|c/|_{p} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 100$$

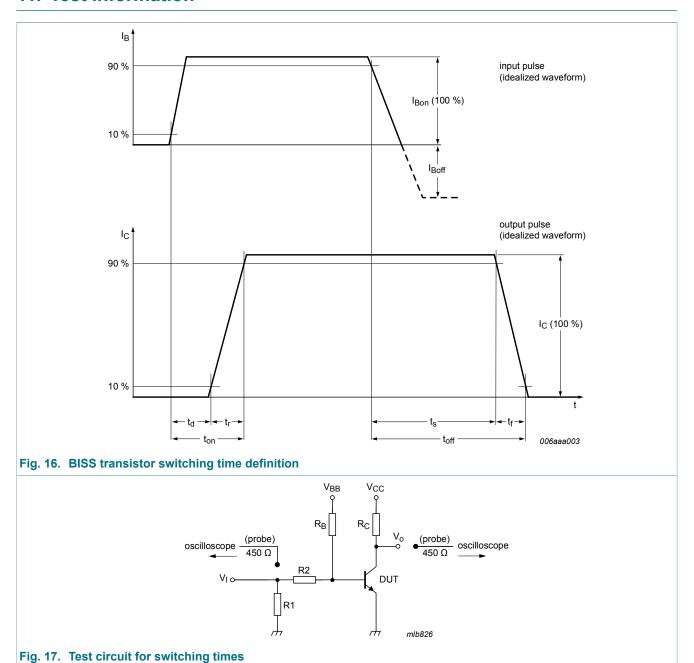
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

30 V, 3 A NPN low VCEsat (BISS) transistor

### 11. Test information

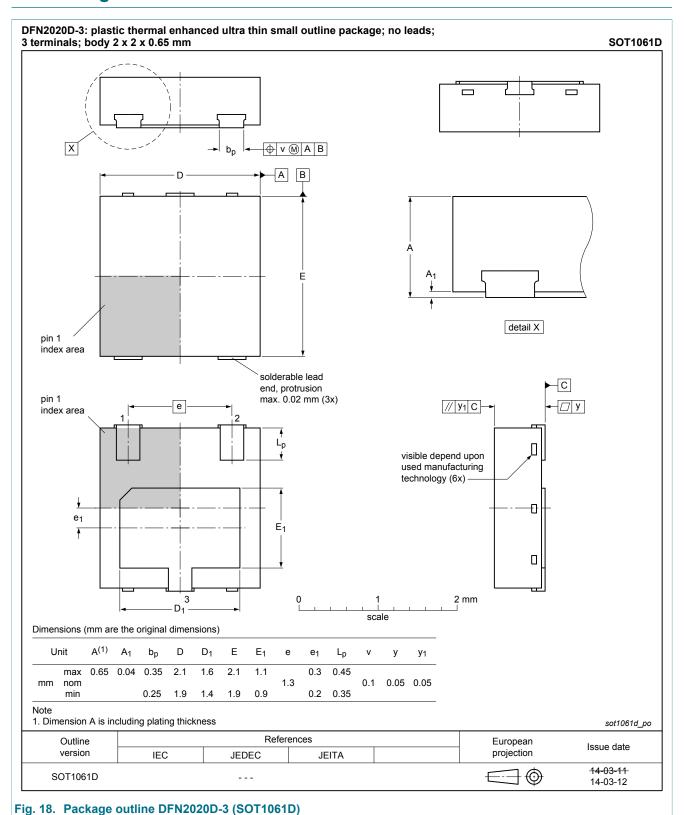


### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

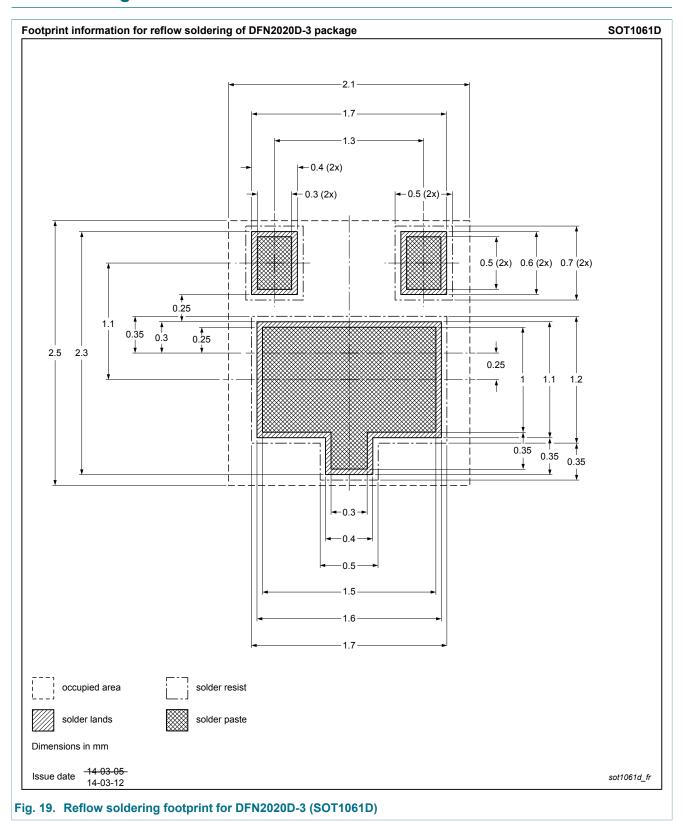
30 V, 3 A NPN low VCEsat (BISS) transistor

## 12. Package outline



30 V, 3 A NPN low VCEsat (BISS) transistor

## 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4330PAS v.1	20140911	Product data sheet	-	-

#### 30 V, 3 A NPN low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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